

# Future Perspective: Sensors and Electronics Integration Frontier

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## Instructions from the organizers:

*"We encourage you to describe ways in which the physics is currently, or will be, enabled by new and creative innovations in electronic instrumentation and methods, rather than giving a historical overview ..."*

**Nygren FEST**  
LBNL, May 2-3, 2014

## Electron – (hole, ion) creation energy $w_i$

	<u><math>w_i</math> [eV]</u>	<u>Application:</u>
Transition Edge Sensors (TES) Superconducting Tunnel Junctions (Bolometers, Microcalorimeters)	$\sim 1-2 \times 10^{-3}$	EM spectrum, meV – keV, eV-resolution spectrometry; precision microcalorimetry
Ge	2.9	Detectors for: x-ray, $\gamma$ -ray spectrometry; Charged particle tracking, <b>Monolithic Active Pixel Sensors</b> ; sampling calorimeters
Si	3.6	
CdTe	5.2	
Diamond	$\sim 13$	
Xe	16	
Kr	19	GeV-TeV calorimetry; Gas and liquid TPCs for detection of neutrinos, nucleon decay, <b>066</b> - decay, dark matter
Ar	24	
Ne	36	
NaI (+PM)	$\sim 200$	SPECT
LSO (+APD, SiPM)	$\sim 100$	PET
PbWSO <sub>4</sub> (+APD)	$\sim 10^5$	GeV calorimetry

# Where is prediction on detectors possible for the next ~ 20 years?

LHC upgrades I and II: Increasing level 1 trigger rate from LAr calorimetry; new all-silicon tracking	$e^+e^-$ collider	e-ion collider	SLHC	TPCs for $0\beta\beta$ -decay, dark matter : scaling up to ton size	LAr TPCs: scaling up to 10-30 kton range	Detectors for astrophysics; photon science
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## Symbiosis of “Sensors” and Microelectronics

- “composite of two species as one unit”; “obligate” – “one cannot exist without the other”

### “Silicon”

- (bump/directly bonded)
- MAPS
- SiPMs

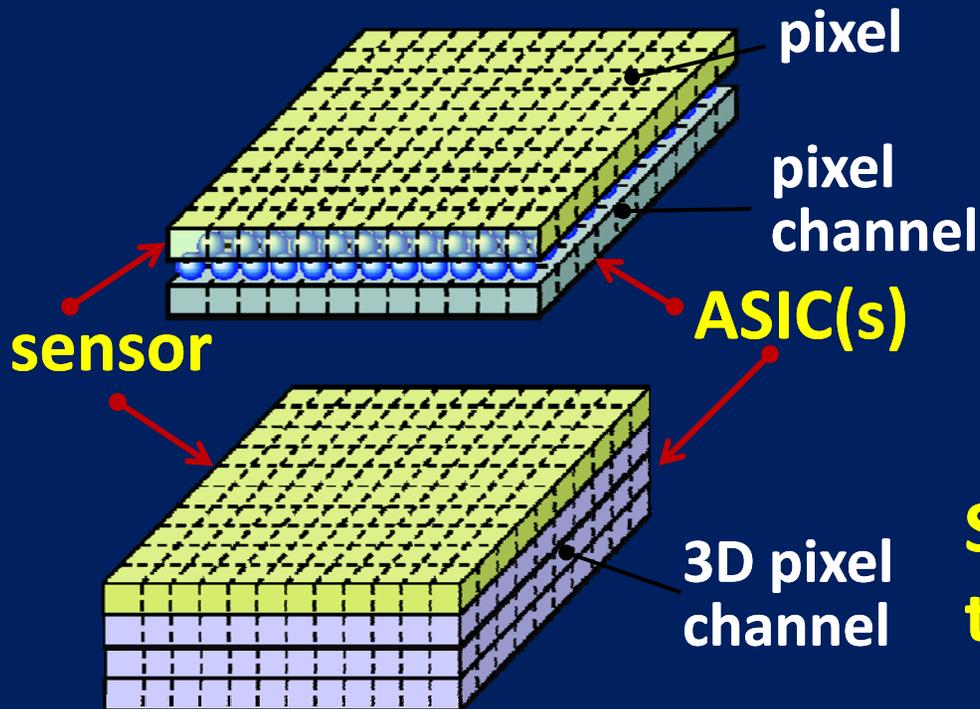
### TPCs

- Gas and liquid, charge and light

### “Microelectronics”

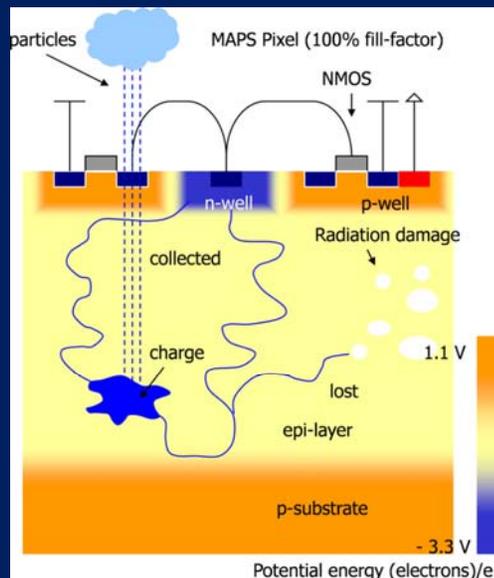
- What after CMOS?

# Si "Pixel" Detectors



Sensor pixels  
bump-bonded to ASIC  
pixels

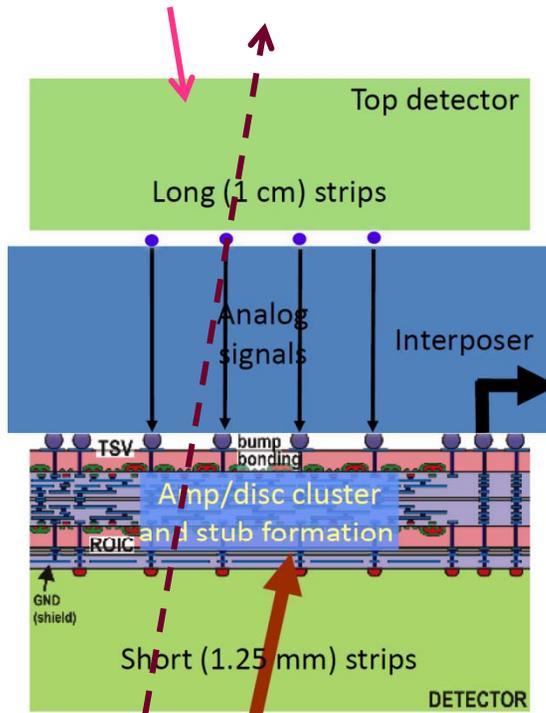
Sensor pixels fusion-bonded  
to (2D or 3D) ASIC pixels



Monolithic Active Pixel  
Sensors (MAPS)

# 3D Integration of Sensors and Readout ICs ("ROICs") - Goals

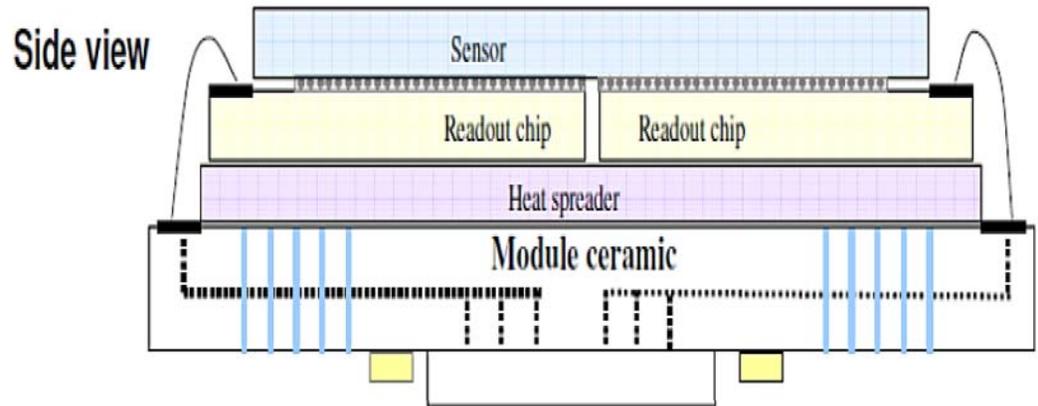
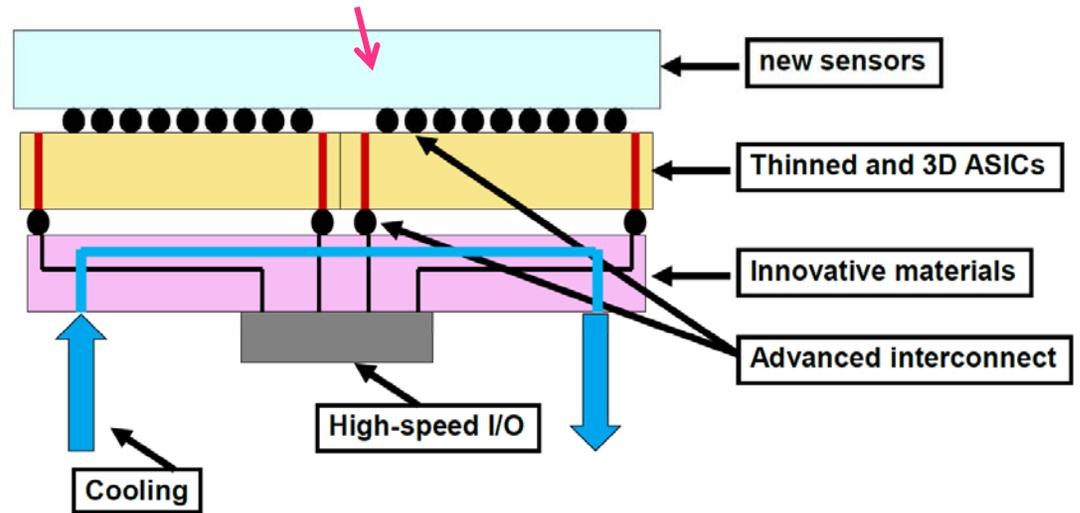
Particle Tracking (ENC~50 e rms)  
Thin sensors (~50-100μm)



ROIC sees signals from top and bottom sensors all correlations local

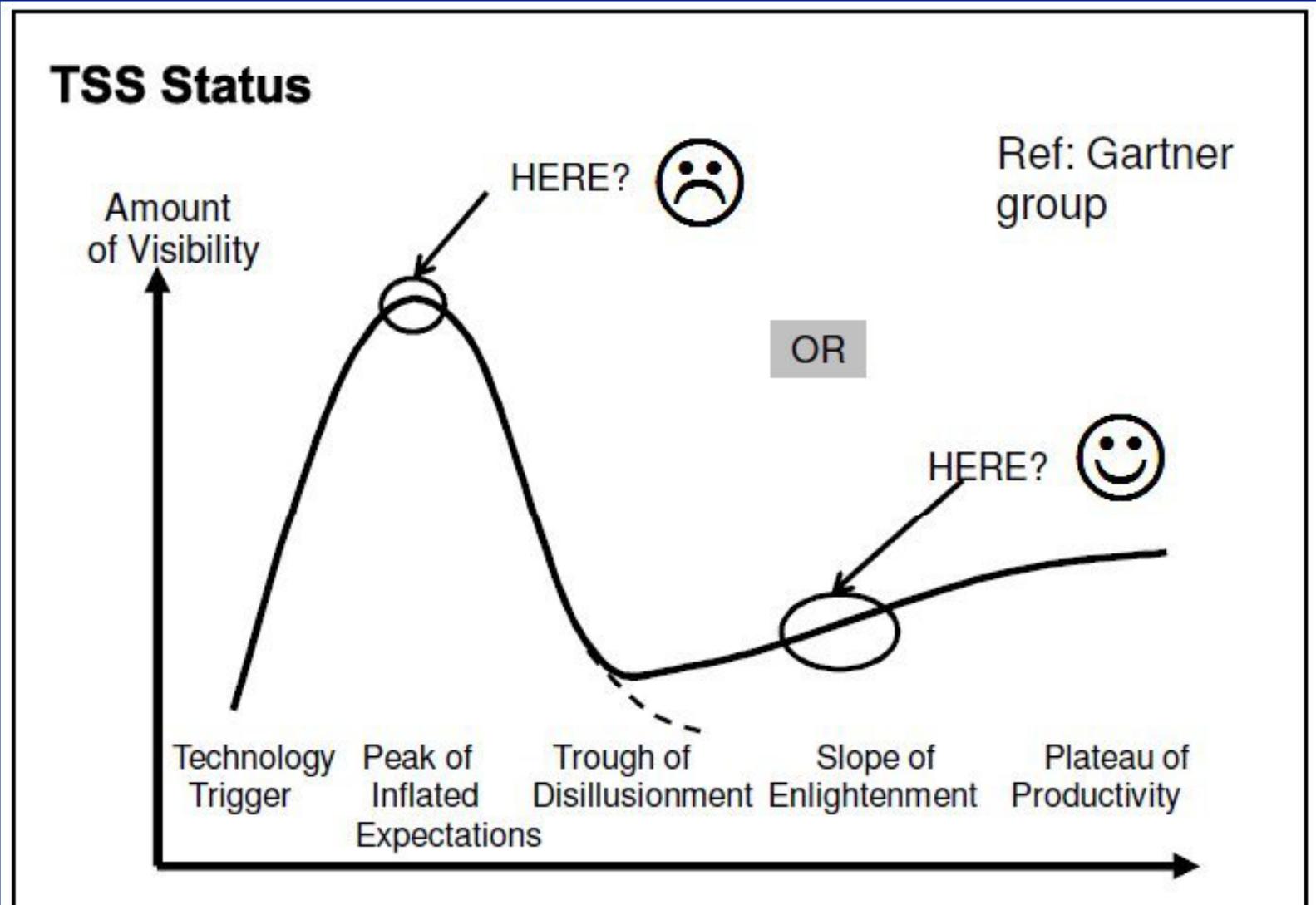
From: G. Deptuch, R. Lipton

X-ray Detectors (ENC<10 e rms)  
Thick sensors (300-500μm)

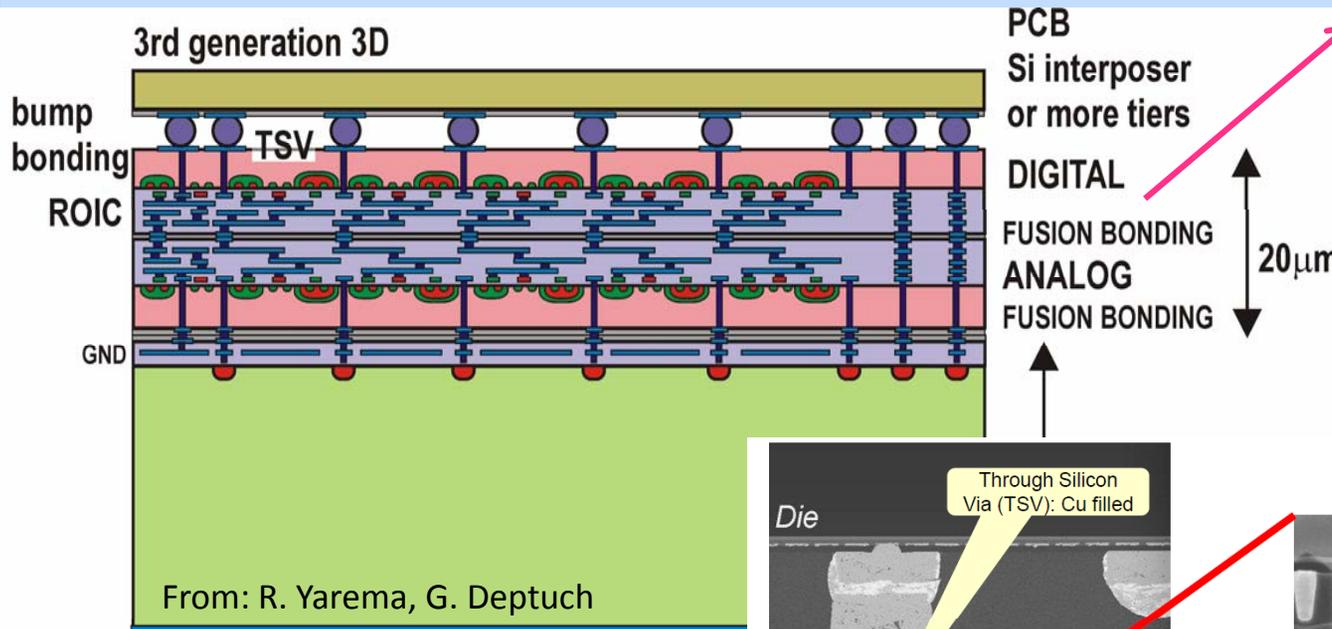


From: H. Grafsmä

# A more sober view ....

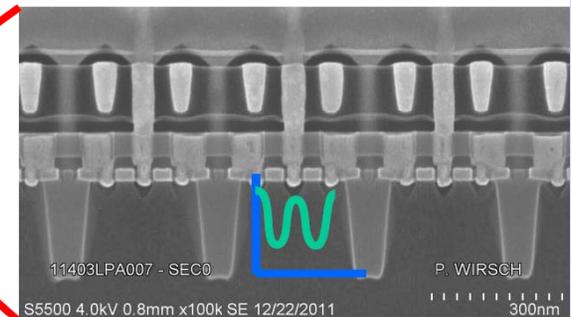
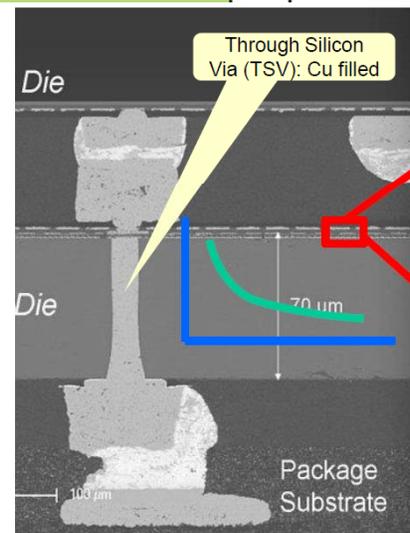


# Technology Challenge → 3D or 2½D?



## Bonding technology:

- Copper to copper
- Oxide to oxide fusion
- Copper to tin
- Polymer/adhesive
- Copper stud



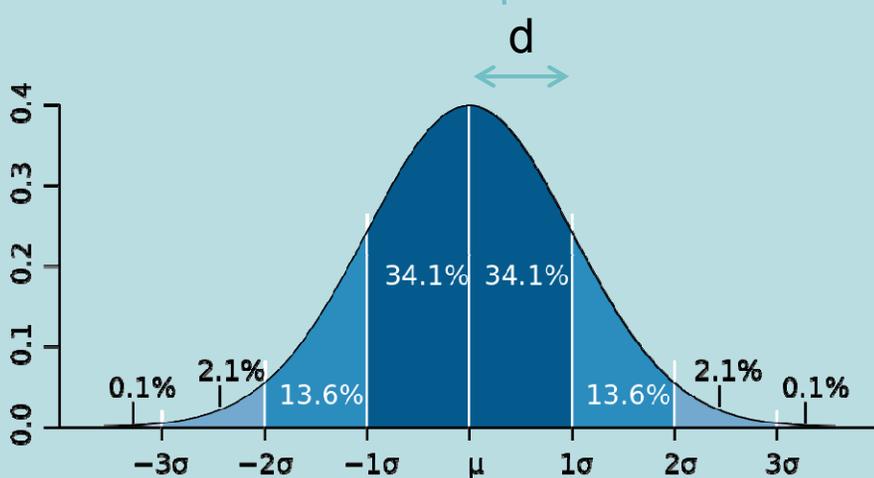
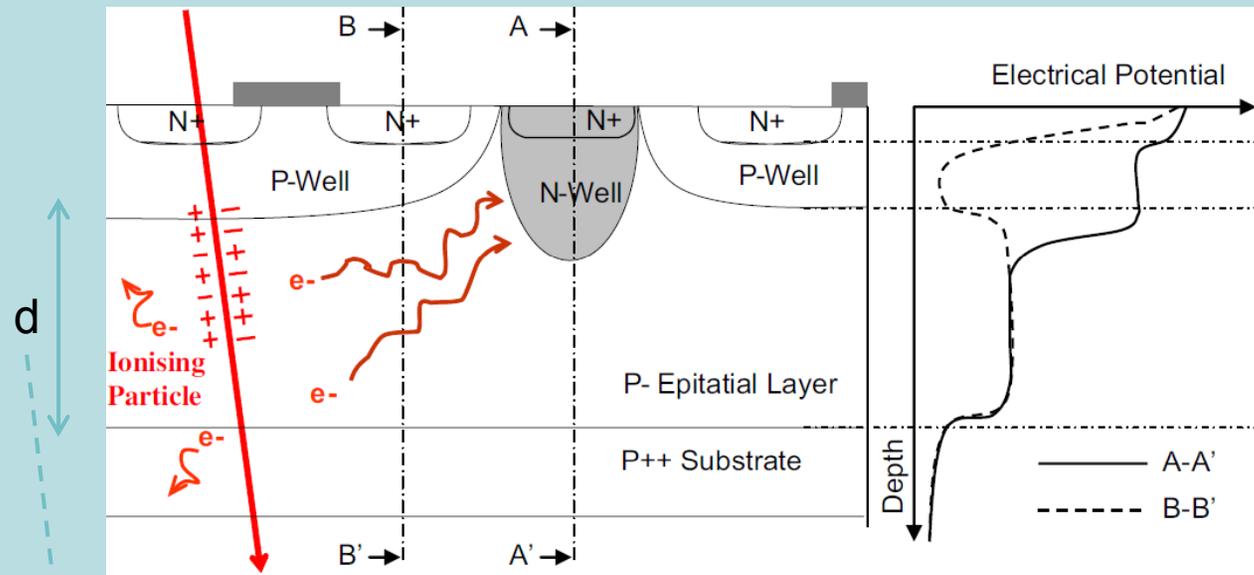
— Expected course of strain (general approach)

## Present industry direction:

- 2½D → no vias in active silicon, only in passive interposers
- 3D → specialized (e.g., memories)

- TSV: μm-range
- Strain engineering @ MOSFETs nm-range

# Charge collection in MAPS (Monolithic Active Pixel Sensors) – sensor and transistors in “standard” CMOS technology



$$\sigma = (2Dt)^{1/2}$$

$$D = \mu \frac{kT}{e}$$

$$t = r^2 / D$$

Diffusion constant (“Einstein 1”)

Diffusion time vs  $r$  (“Einstein 2”)

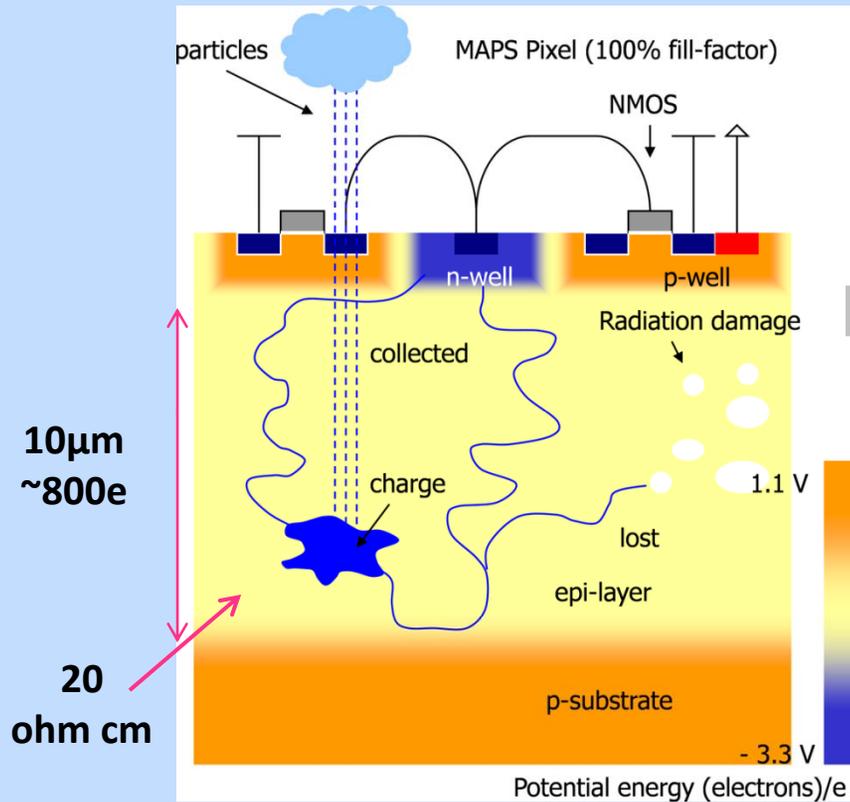
$\approx 15\text{ns}$  to diffuse to  $10\mu\text{m}$ ;

$\approx$  **135ns to 30 $\mu\text{m}$**  in silicon.

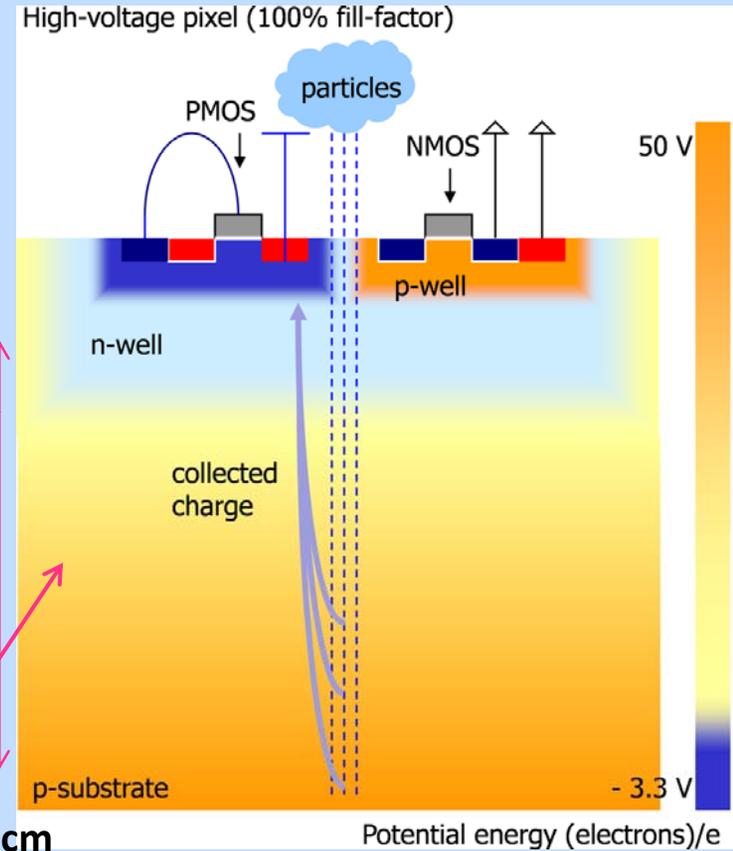
Drift time for electrons and holes  $\sim 1/v_{drift}$ ,

$\sim < 10\text{ns}$  for  $100\mu\text{m}$

# MAPS: From Charge Diffusion to Drift



25-50  $\mu\text{m}$   
2-4ke



**Challenge: How to do it in a "standard" process?**

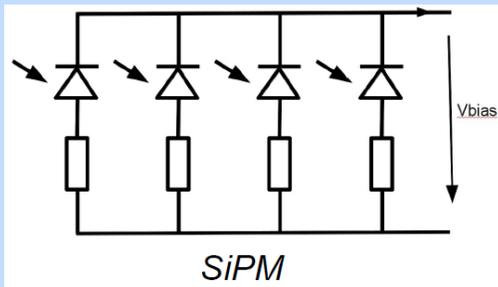
- Better S/N
- Shorter charge collection time
- Higher radiation tolerance

Adapted from: I. Peric

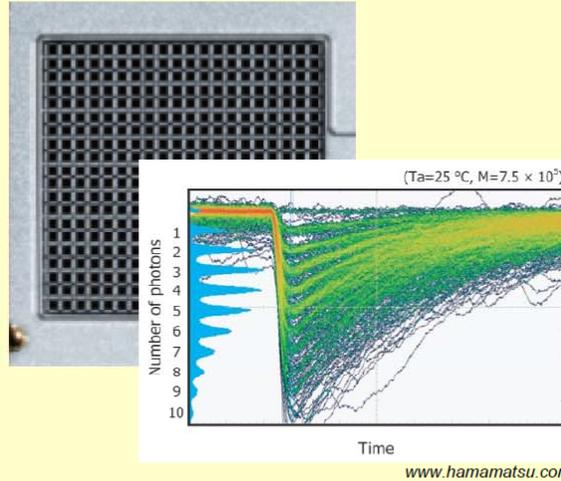
<http://sus.ziti.uni-heidelberg.de/Forschung/FGDetektoren/SDA/?lang=en>

# Silicon Photo Multipliers (SiPMs) – Geiger-mode Avalanche Photo Diodes

**Passive quenching**

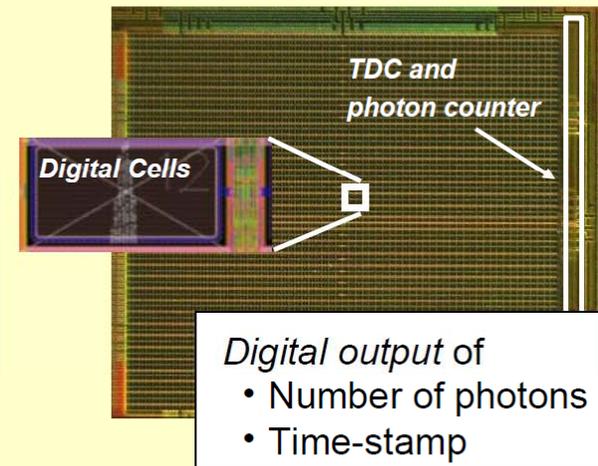


## Analog SiPM



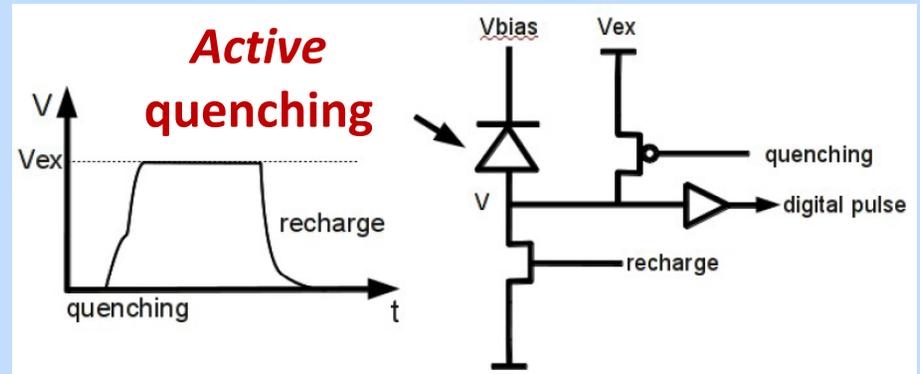
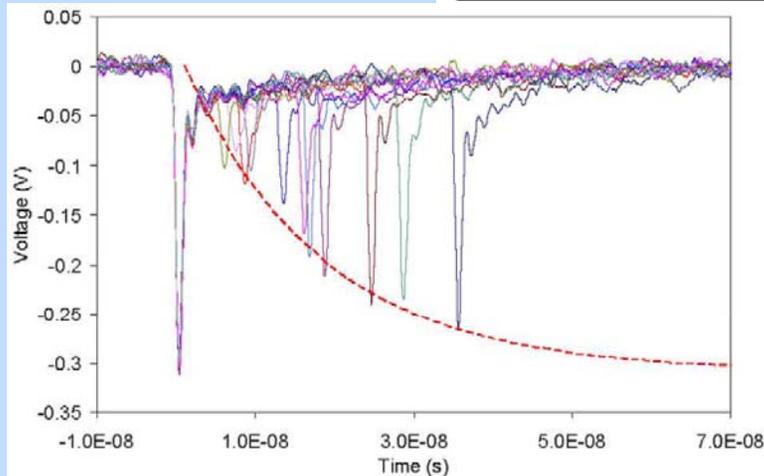
- Cells connected to common readout
- Analog sum of charge pulses
- Analog output signal

## Digital SiPM



- Number of photons
- Time-stamp

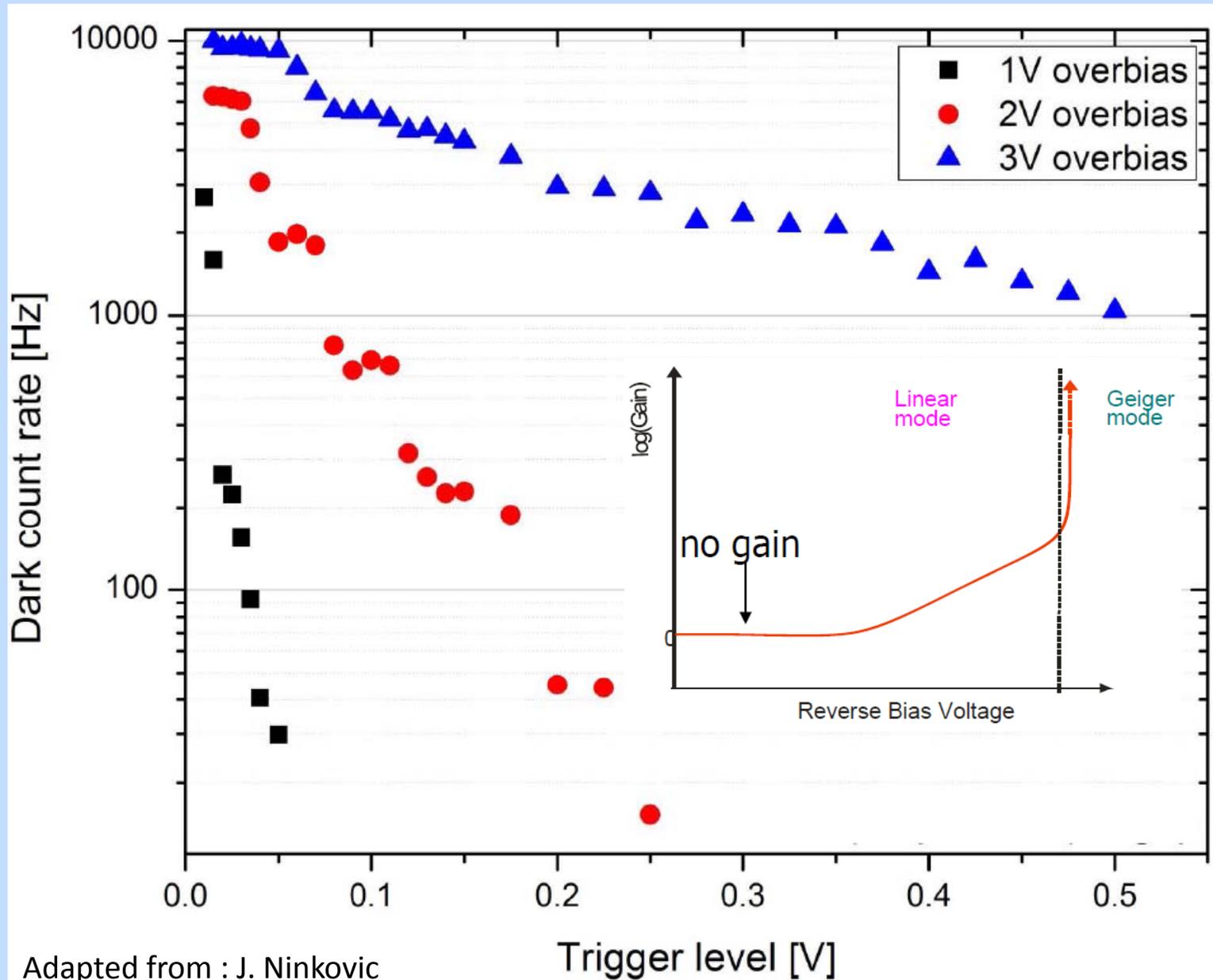
- Each diode is a digital switch
- Digital sum of detected photons
- Digital data output



**Active quenching**

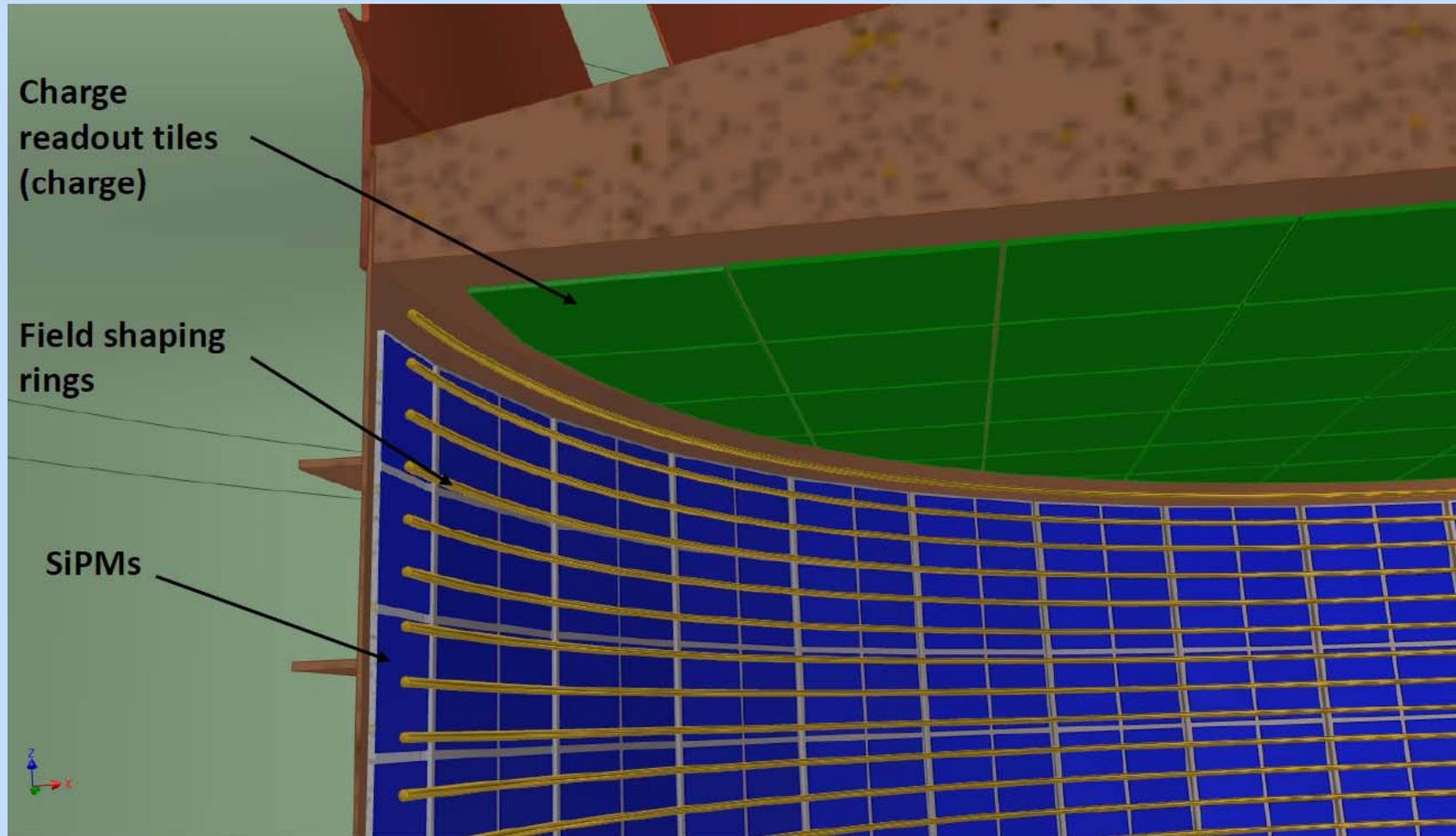
Adapted from : T. Frach et al.

# SiPMs: “Dark” Noise and Optical Crosstalk → Active Quenching



Adapted from : J. Ninkovic

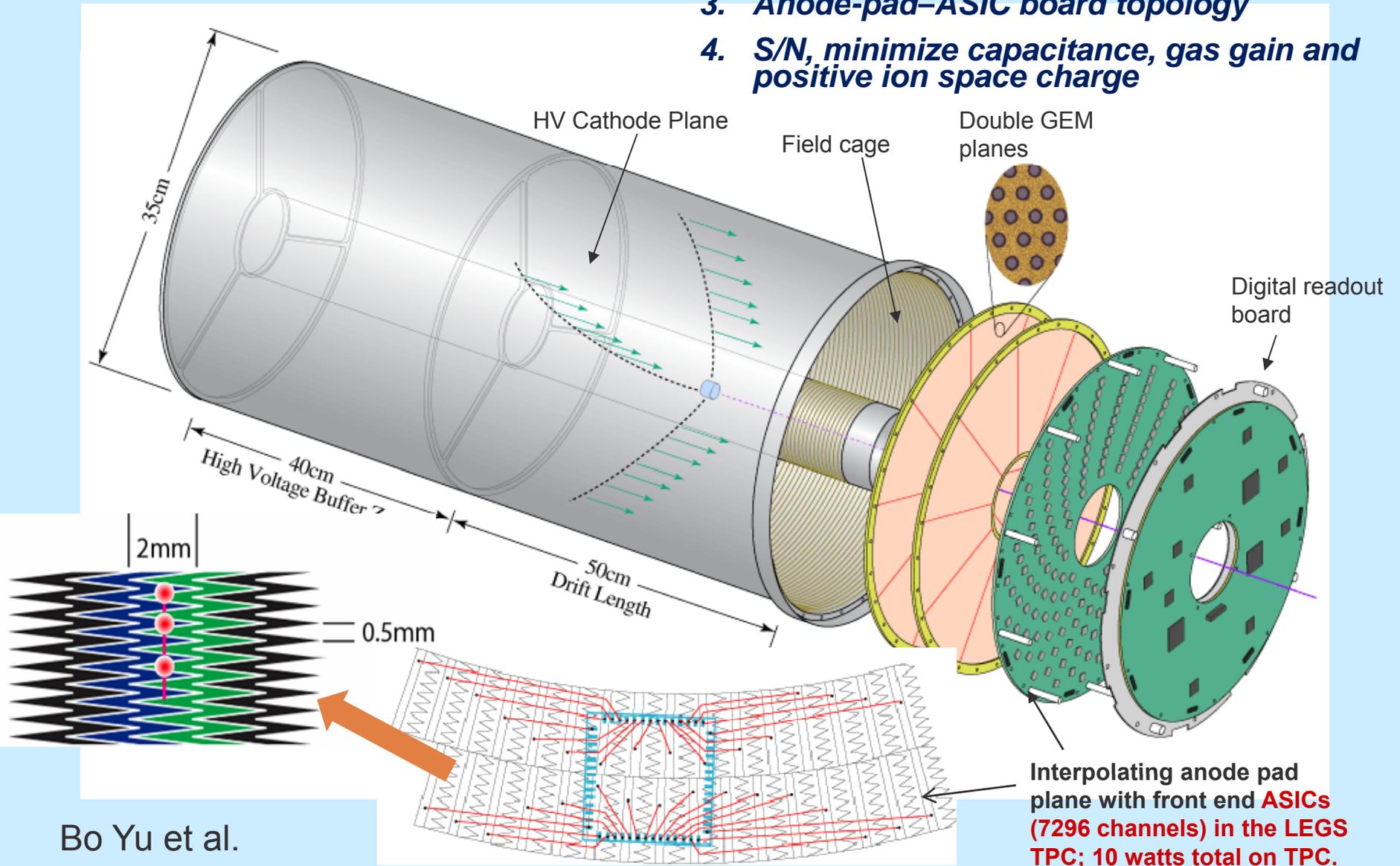
## Challenge: SiPMs to cover large areas ...



- Light collection on the barrel behind field shaping rings

# Fine Granularity Gas TPCs:

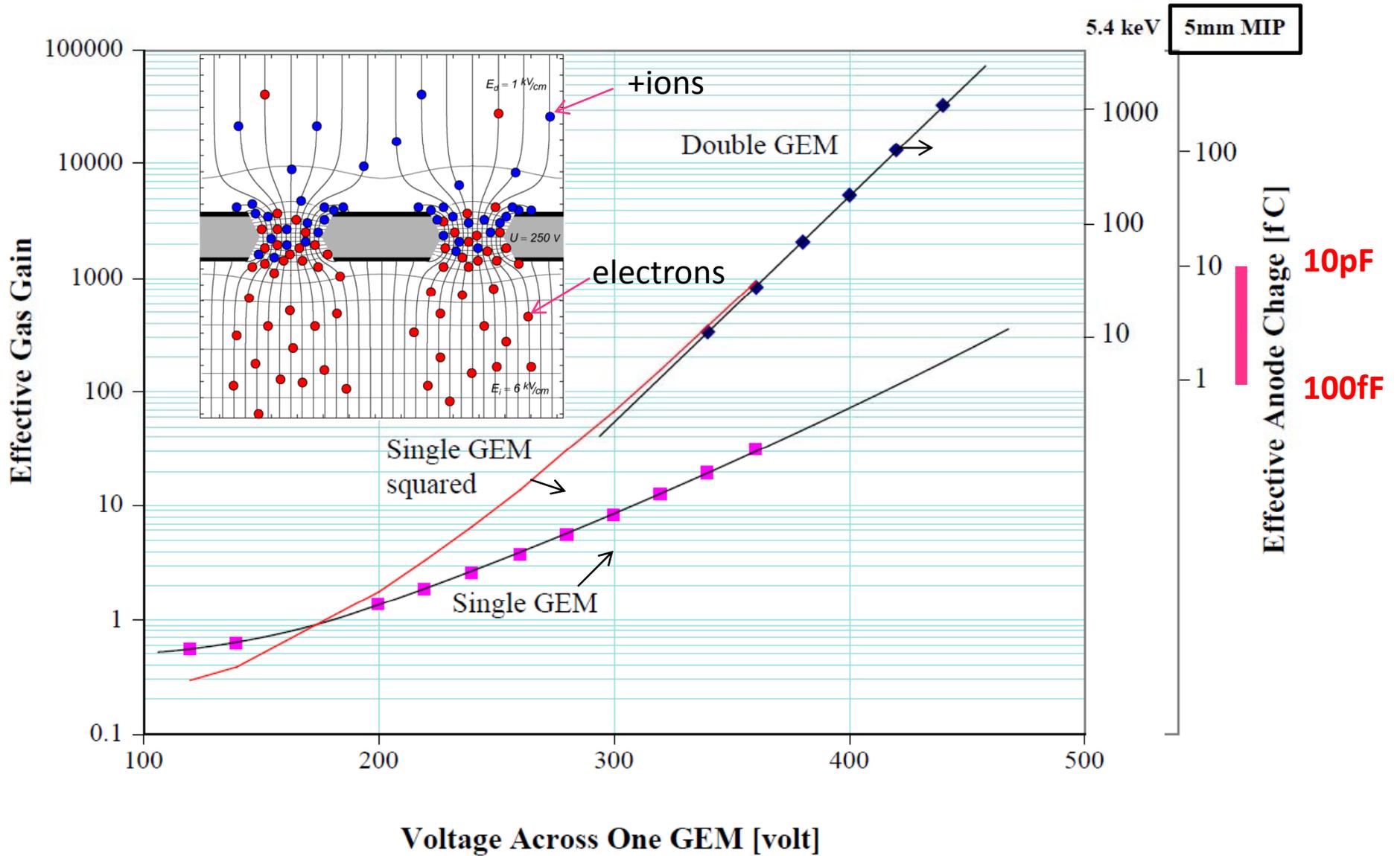
1. **GEM vs Micromegas**
2. **Interpolating anode configuration - chevron**
3. **Anode-pad-ASIC board topology**
4. **S/N, minimize capacitance, gas gain and positive ion space charge**



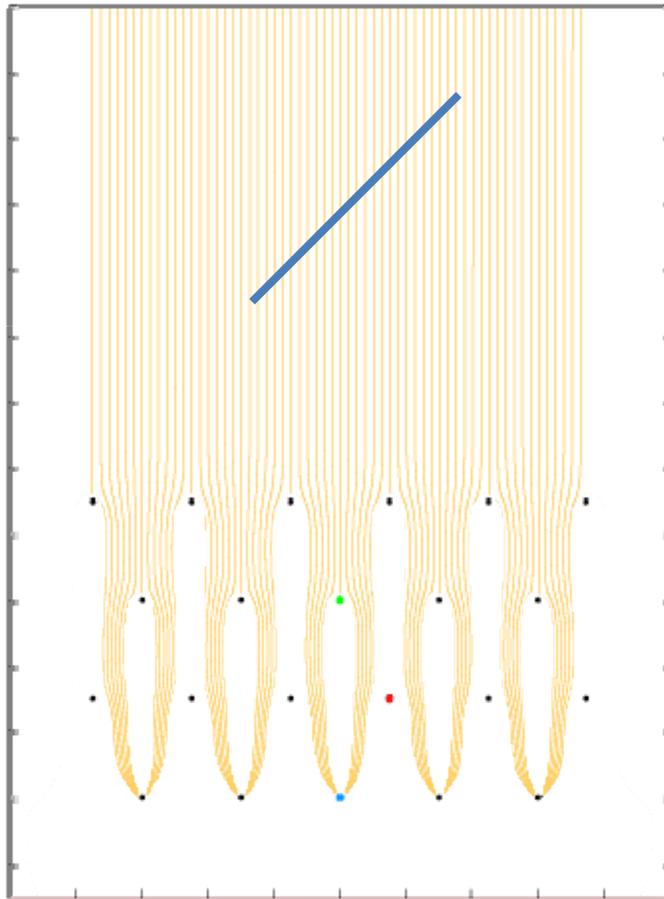
Bo Yu et al.

# Effective Gas Gain of the Double GEM Detector

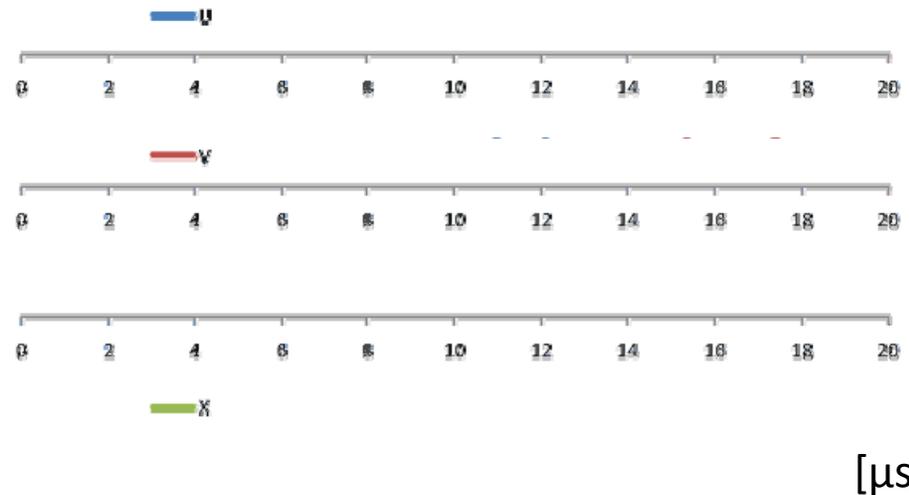
Ar+20% CO<sub>2</sub>, 5.4 keV x-rays (~1mm<sup>2</sup>, 2kHz), E<sub>d</sub>=1kV/cm, E<sub>t</sub>=4kV/cm, E<sub>i</sub>=5kV/cm



# Signal Formation on Wire Electrodes in Noble Liquid TPCs: Induced Signals from a Track Segment

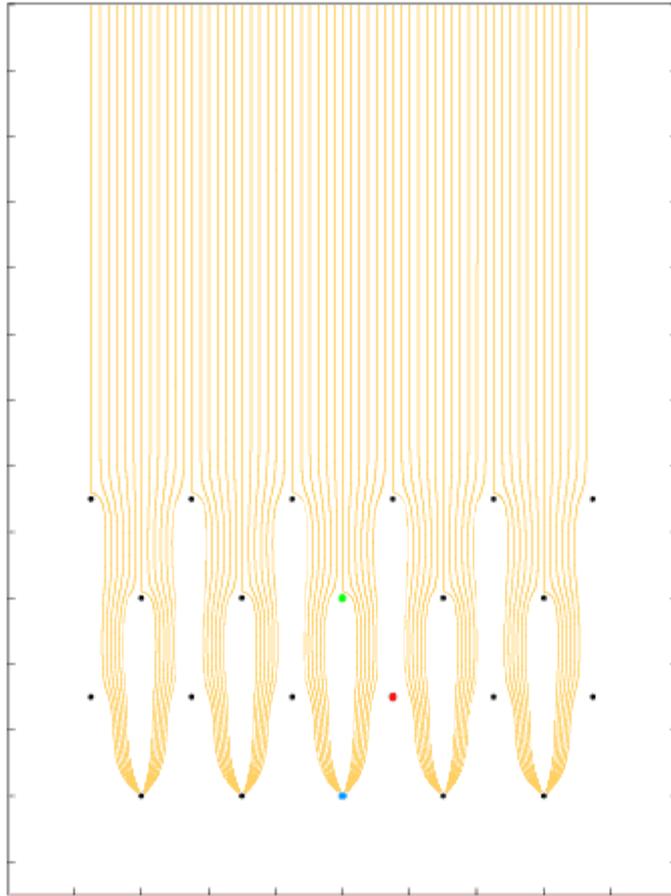


*Time scale* is determined by the electron drift velocity and wire plane spacing (3 mm shown)

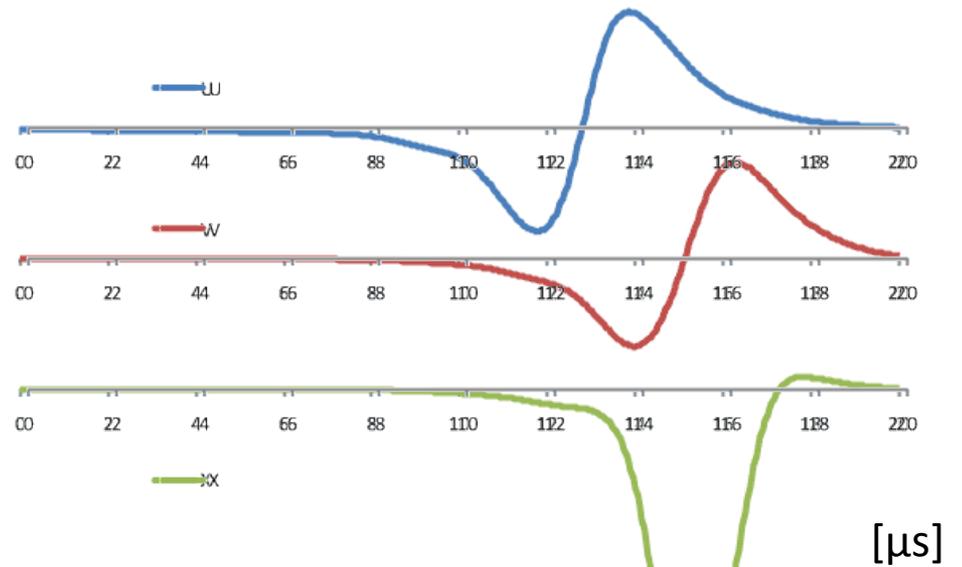


LBNE style wire arrangement: 3 instrumented wire planes + 1 grid plane  
Raw current waveforms convolved with a 0.5  $\mu\text{s}$  gaussian ( $\sim 1/2$  drift length) to mimic diffusion

# Signal Formation on Wire Electrodes in Noble Liquid TPCs: Induced Signals from a Track Segment



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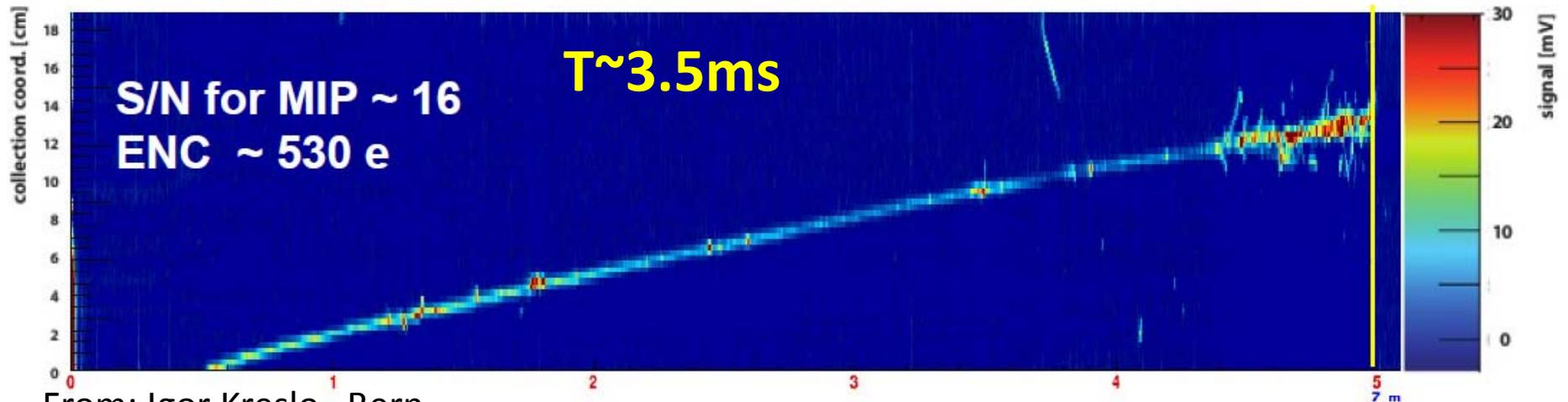
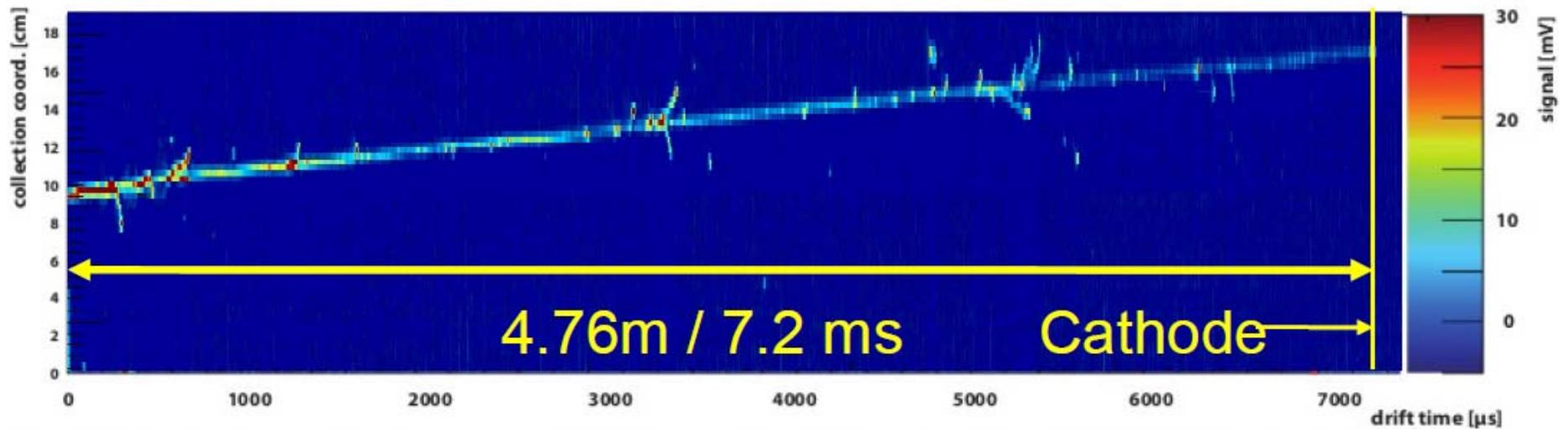


LBNE style wire arrangement: 3 instrumented wire planes + 1 grid plane  
Raw current waveforms convolved with a  $0.5\mu\text{s}$  gaussian ( $\sim 1/2$  drift length) to mimic diffusion

# Testing MicroBooNE cold preamps with ARGONTUBE

~ 5 m long electrons drift in LAR: first time!

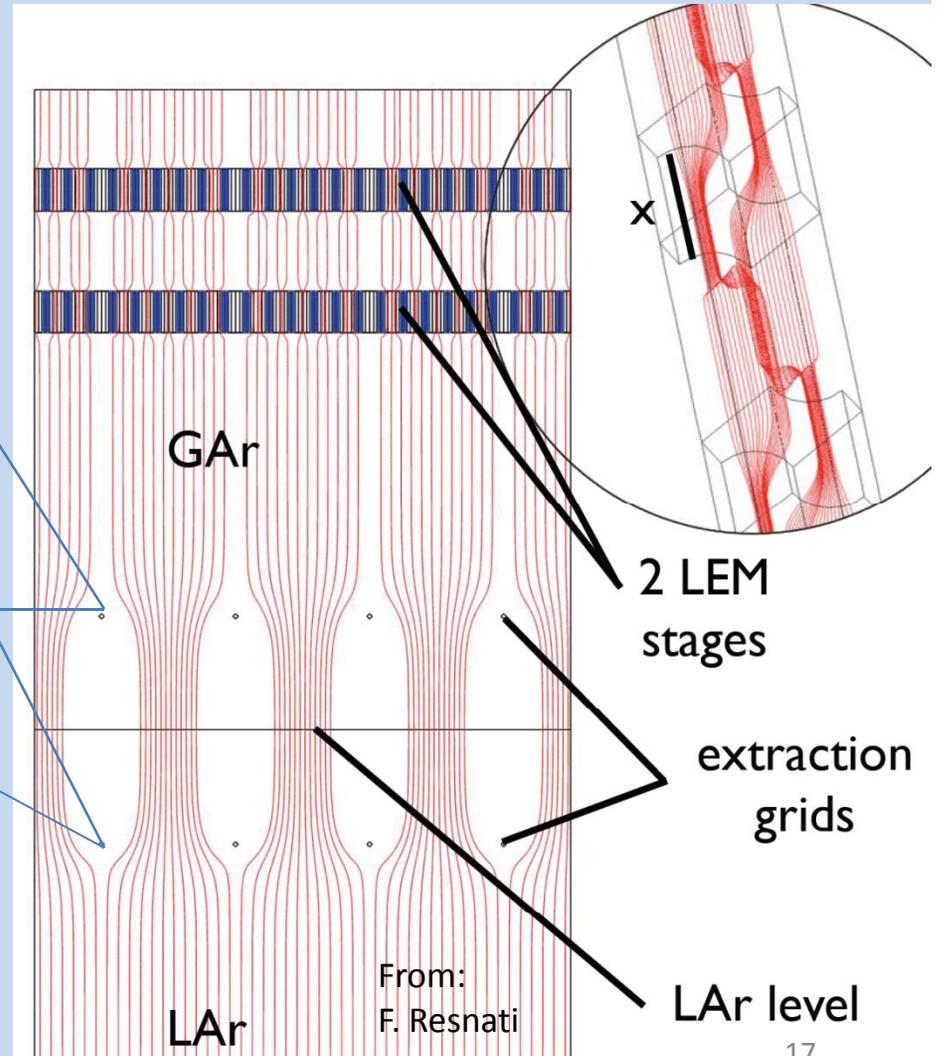
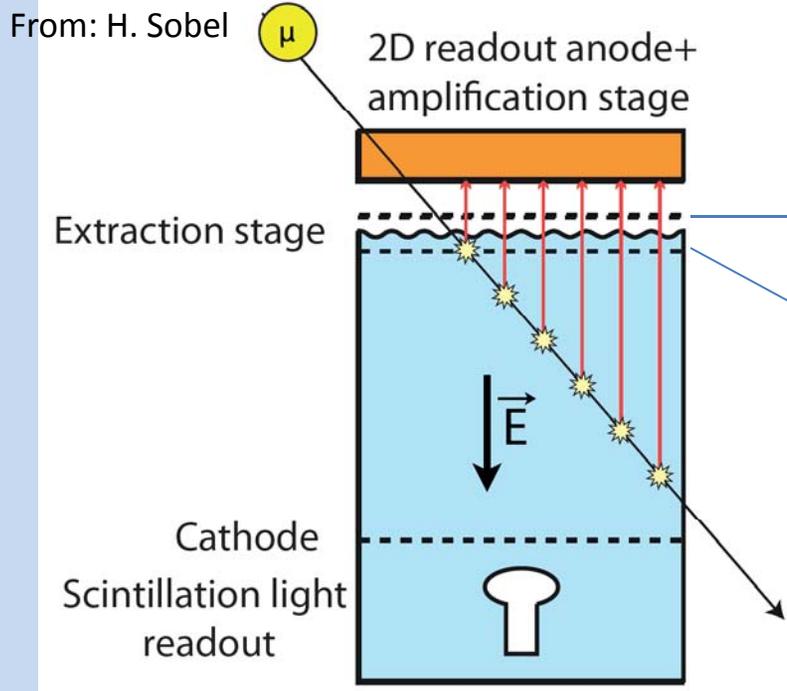
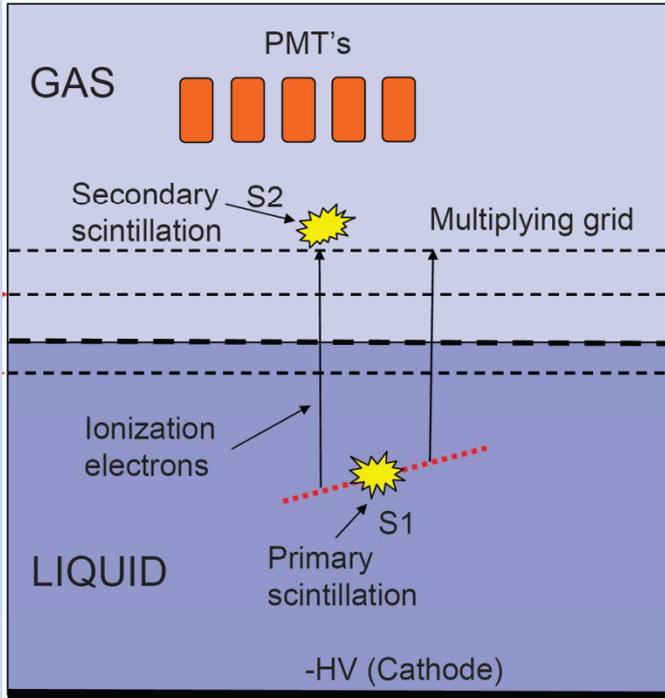
twice MicroBooNE drift length, <math>\lt; \frac{1}{2}</math> E-field



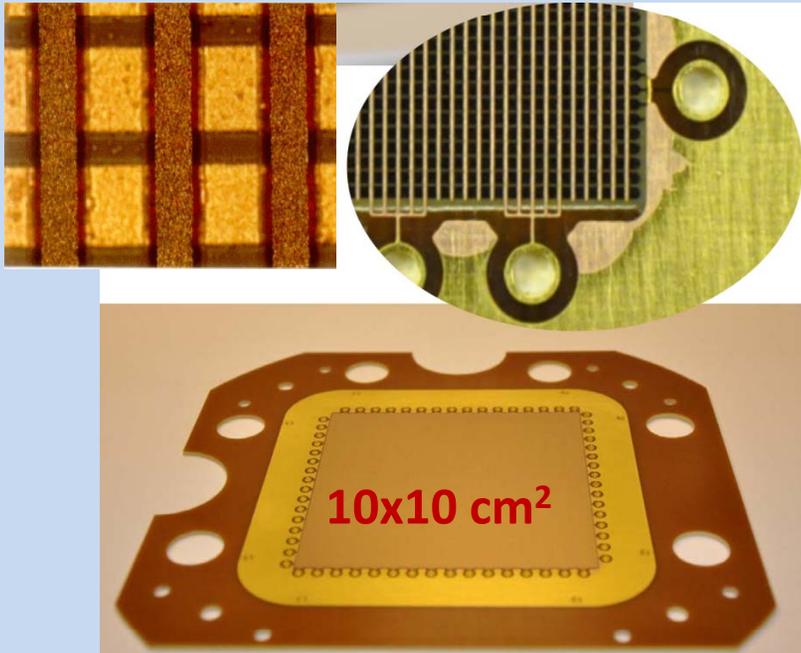
From: Igor Kreslo, Bern

# Dual-Phase Noble Liquid-Gas Detectors:

Small (multi-ton) for Dark Matter (WIMP) detection *and* Large (multi-10 kton) for neutrino studies, proton decay, neutrinos from SN

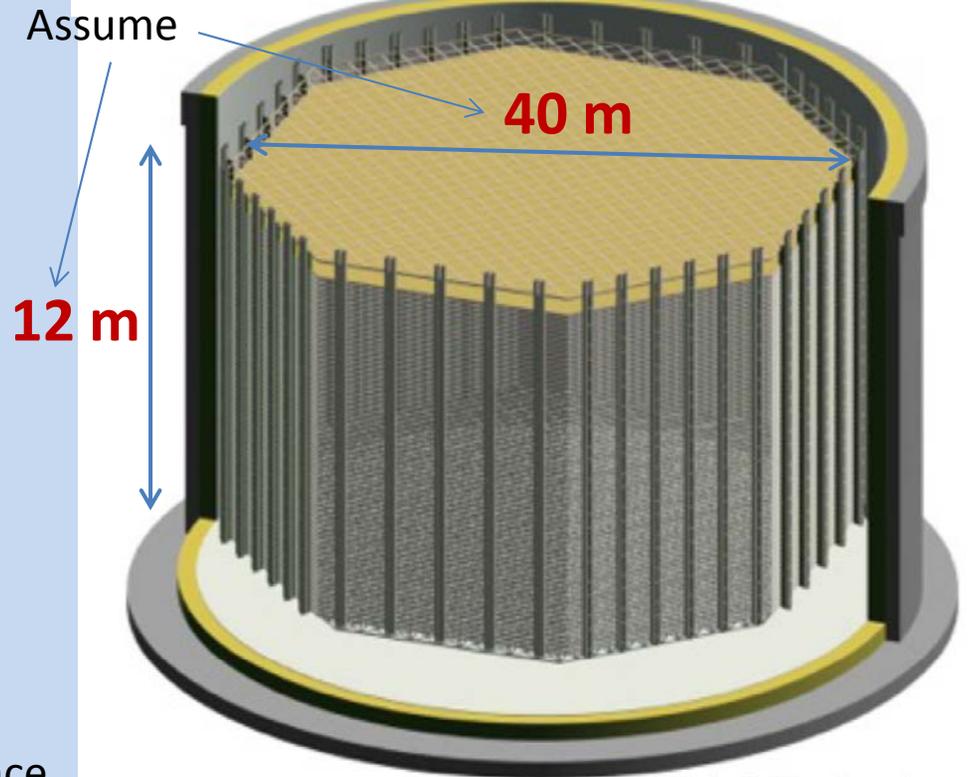


# Large Two-Phase LAr TPCs: The Challenge of Scaling up Readout Electrodes



From: F. Resnati

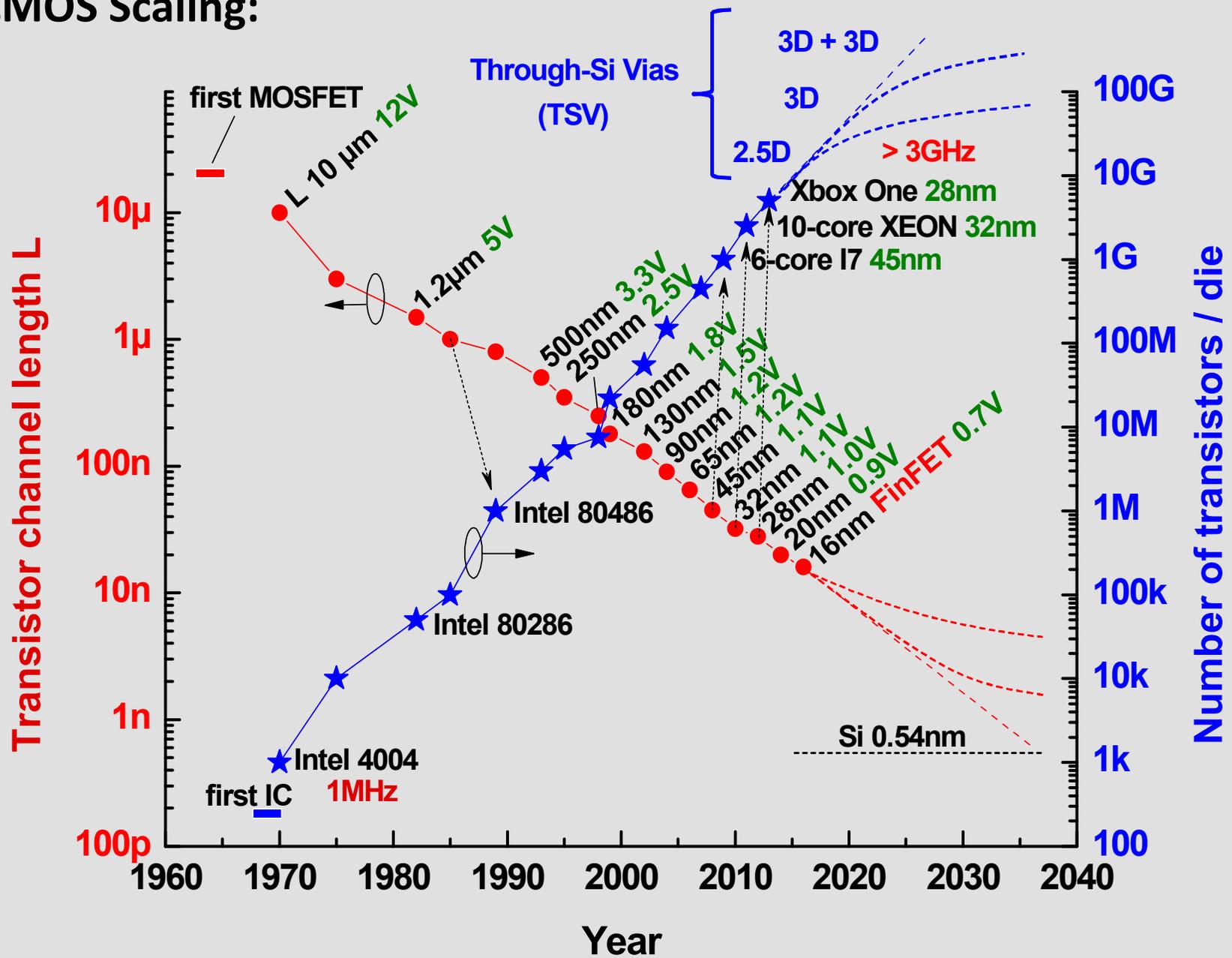
- X-Y strip electrodes have a large capacitance
- above  $\sim 100\text{-}200$  pF per 1 m strip, the S/N is affected
- signal channels:  $\approx 400/\text{m}^2 \rightarrow > 5 \times 10^5$  for  $\sim 20$  kton with 12m drift ( $\sim 25$  strips-channels/ton, nearly the same as for LBNE with 2.5 meter drift distance)
- Cold electronics with multiplexing clearly needed
- Electron multiplication leads to loss of easy charge calibration inherent to ion chambers



20 kT design

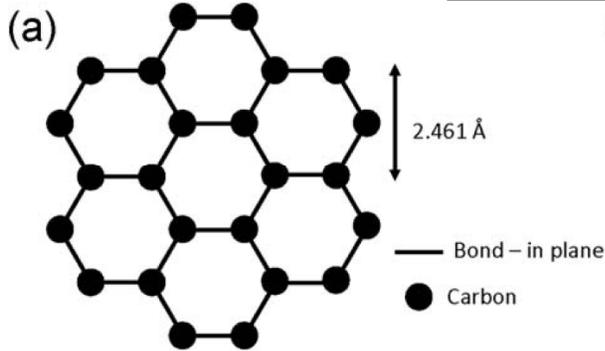
A scaled down  
LAGUNA concept  
From: A. Rubbia, A.  
Ereditato  
Aiming at  $\geq 100$  kton

# CMOS Scaling:



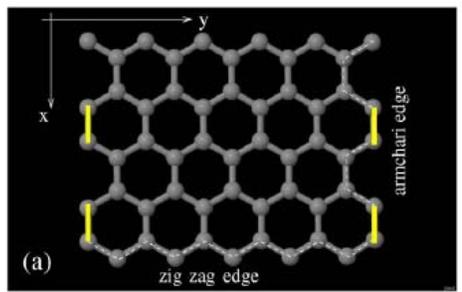
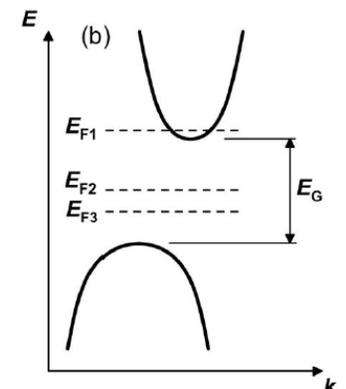
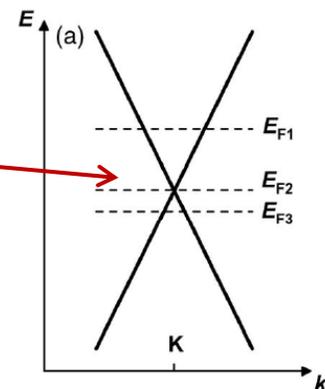
# The promise of *graphene* ...

**Electron mobility:  $>10^5$  !!!**

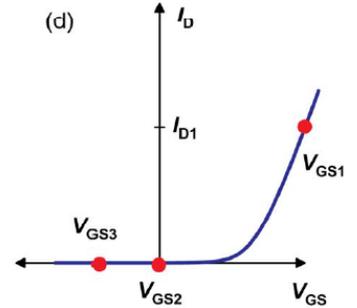
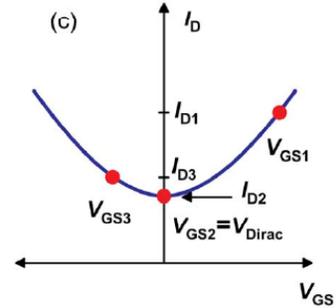


A. Hsu et al.

**“Details”:**  
 - Bandgap  $\rightarrow 0$   
 - contact resistance high

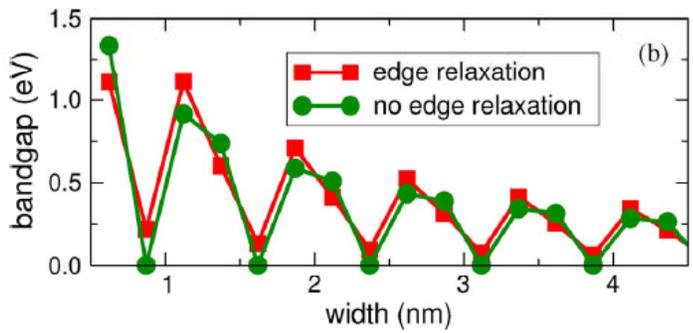


Bandgap is “induced” in a ribbon, but mobility drops ...



**Graphene MOSFET:**  
 - Not a switch  
 - RF amplifier, yes

**Si-MOSFET**  
 From: F. Schwierz

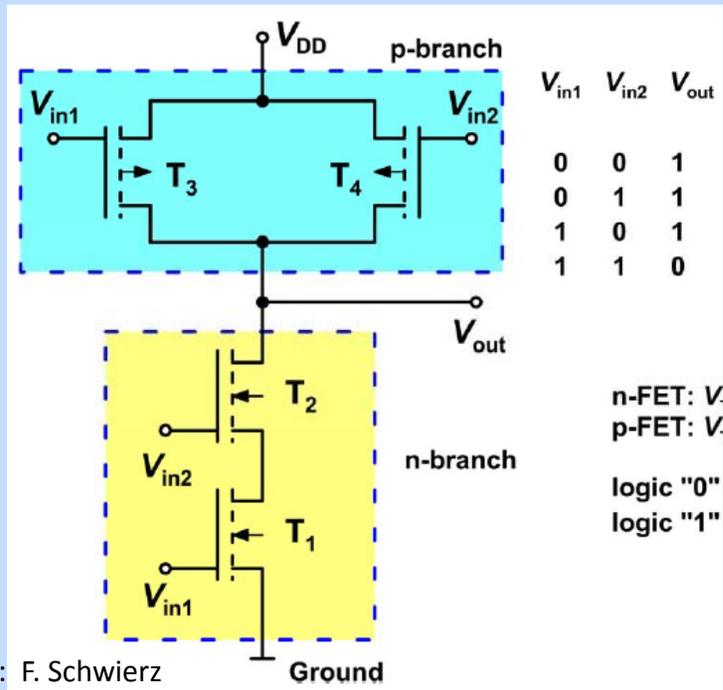


From: G. Fiori, G. Iannaccone

Graphene issue:  
 PROCEEDINGS OF THE IEEE | Vol. 101, No. 7, July 2013

# Beyond CMOS?

CMOS NAND Gate:



From: F. Schwierz

Any "Beyond CMOS" device should have many of the same characteristics as CMOS devices :

- power gain  $>1$
- ideal signal restoration and fanout
- high ON/OFF current ratio  $\sim 10^{5-7}$
- low static power dissipation
- compatibility with Si CMOS devices for mixed functions

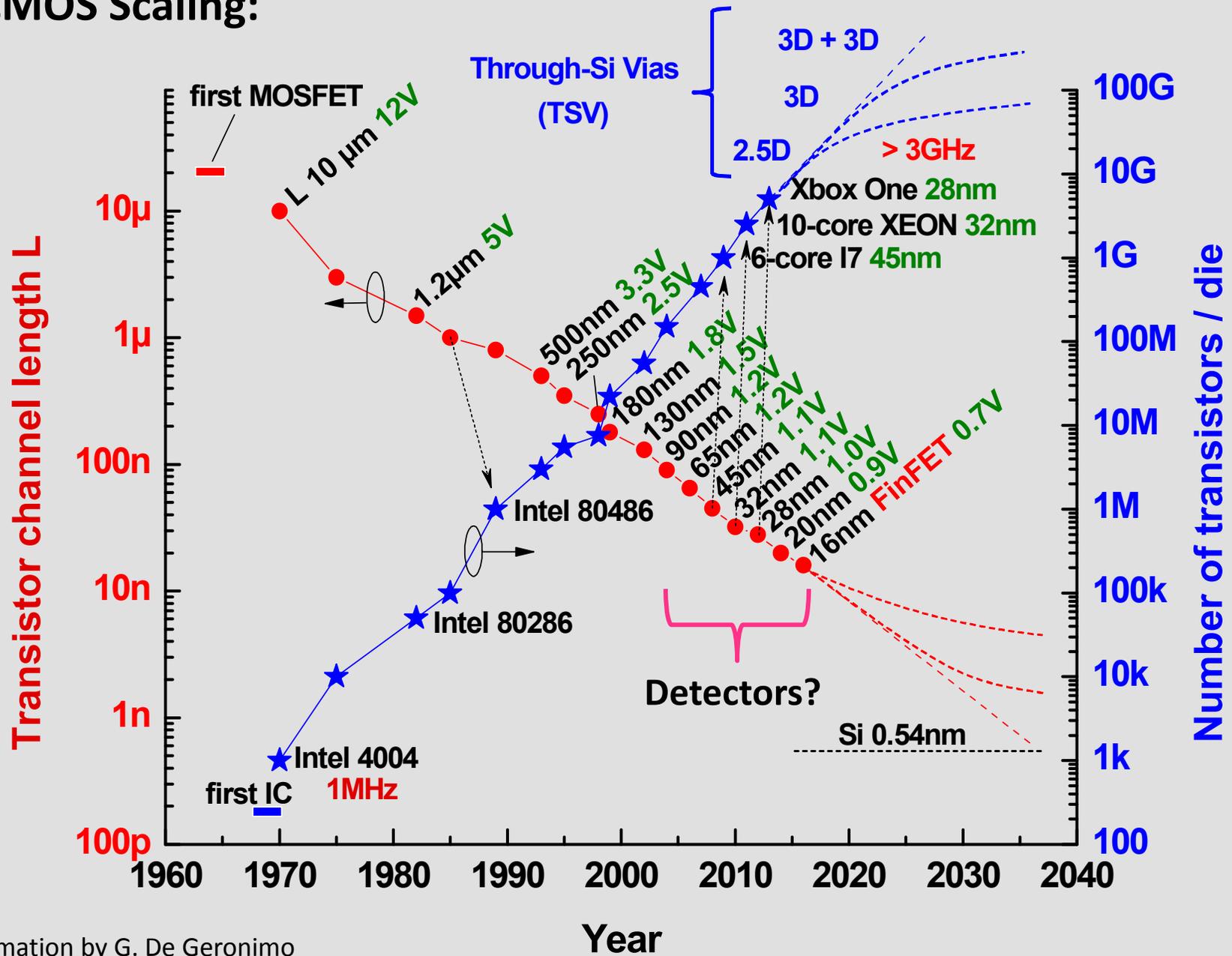
Physical (computational) variables:  
charge, current, voltage, electric dipole, magnetic dipole, orbital state

Devices considered by NRI:

- tunnelling FET
- graphene nanoribbon FET
- bilayer pseudospin FET
- SpinFET
- spin transfer torque/domain wall
- spin majority gate
- spin transfer torque triad
- spin torque oscillator logic
- all spin logic device
- spin wave device
- nanomagnet logic
- III-V tunnel FETs

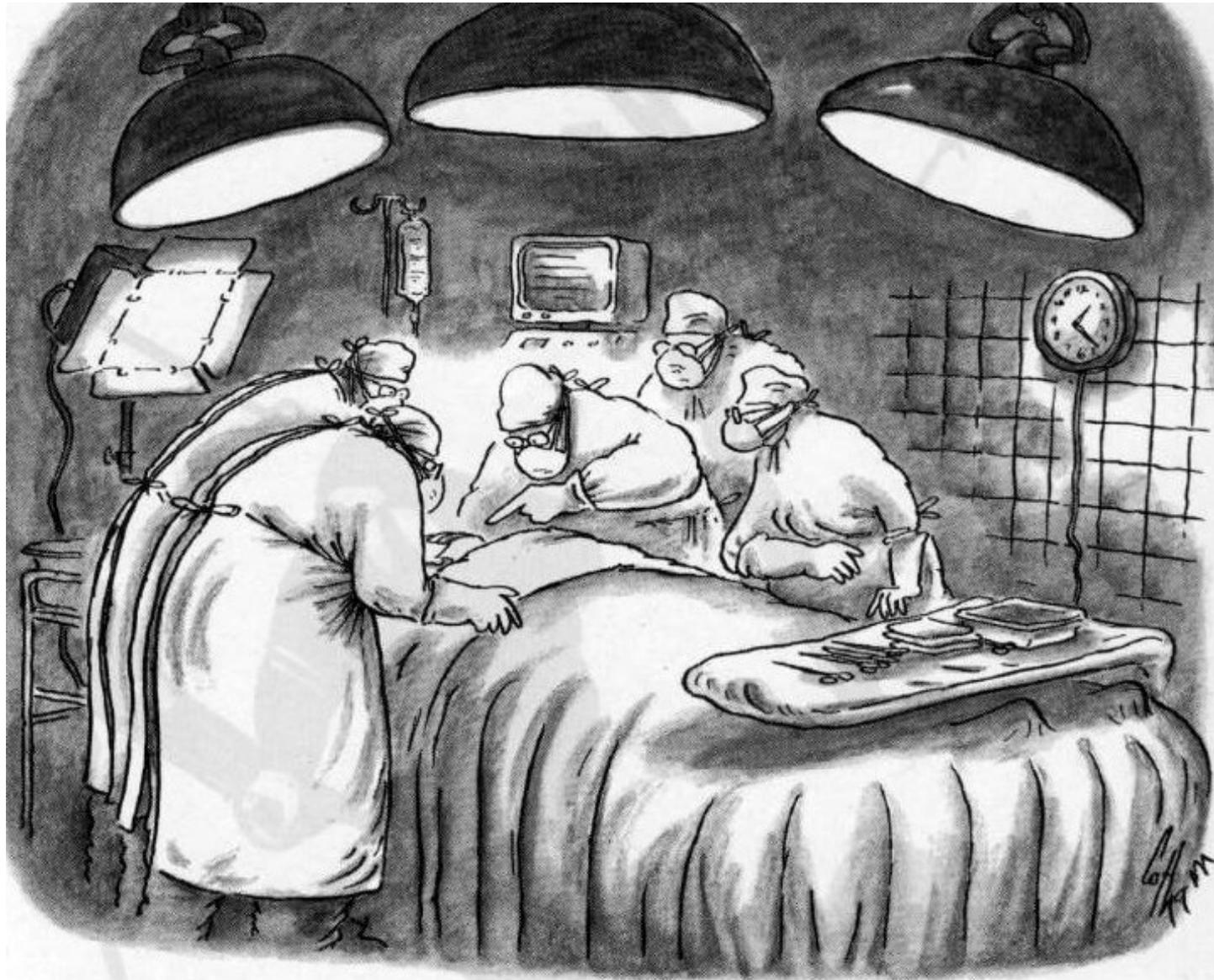
Upon analysis: Spintronic devices have longer switching delays and higher switching energies, due to inherent time of magnetization propagation ...

# CMOS Scaling:



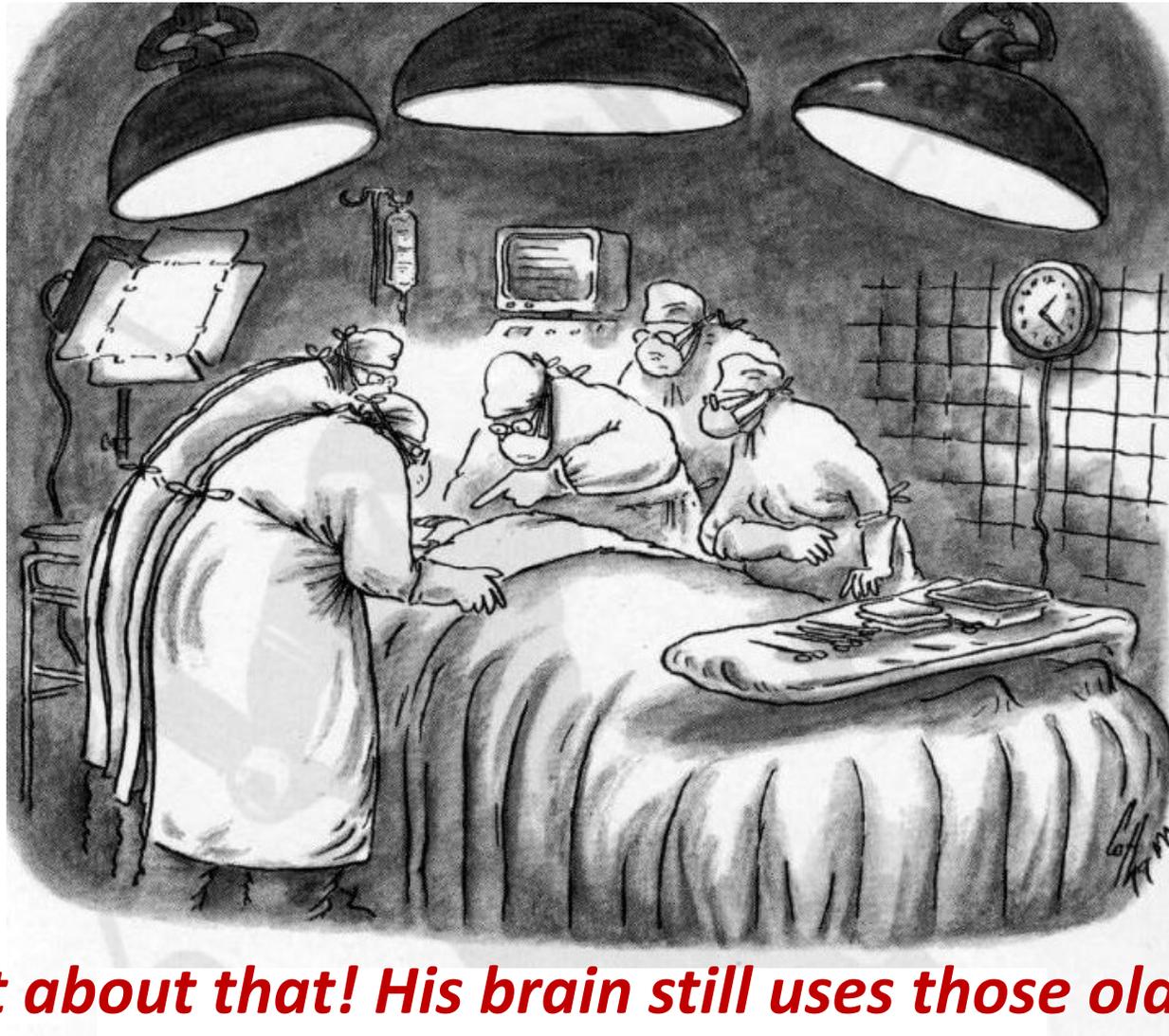
Information by G. De Geronimo

*After the transistor revolution:*



*“What about that! His brain still uses the old vacuum tubes.”*

*It will be some time before the cartoon reappears:*



***“What about that! His brain still uses those old CMOS 3D systems on chip.”***

## *Creating fertile ground for future Nygrens*

The gas TPC was a unique breakthrough idea - its value has been growing due to its continuing evolution. The current and future activity on numerous gas and liquid TPCs is the best tribute to David.

To continue in David's tradition with the next generation of detector researchers, some thought will have to be devoted how to maintain a climate favorable to creation and pursuit of new ideas.

In addition to carefully planned R&D programs under tight funding conditions and the resulting oversight, the burden will be on research institutions to provide continuity and a degree of freedom. A difficult task that will require considerable vision from the future laboratory leaders ...